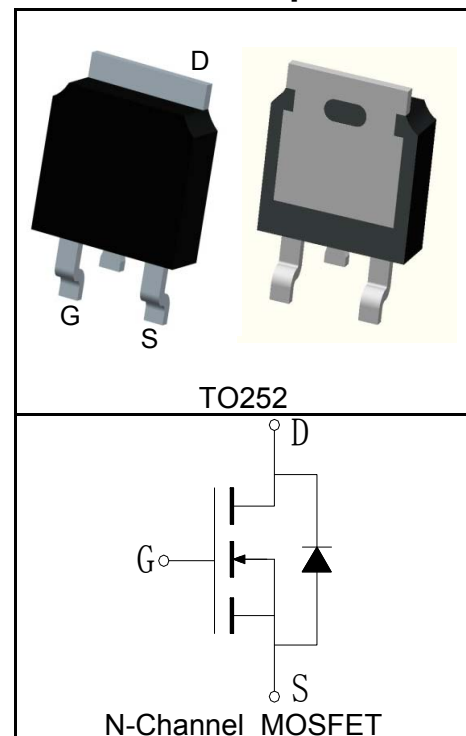


**Features**

- 30V/50A
- $R_{DS(ON)} = 4.8m\Omega(Typ.)@V_{GS}=10V$
- $R_{DS(ON)} = 6.8m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- Fast Switching Speed
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

**Applications**

- DC/DC Converters
- On board power for server
- Synchronous rectification

**Pin Description**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_C=25^\circ C$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	175	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ C$ 50	A
<b>Mounted on Large Heat Sink</b>			
$I_{DP}^{①}$	300 $\mu s$ Pulse Drain Current Tested	$T_C=25^\circ C$ 200	A
$I_D^{②}$	Continuous Drain Current( $V_{GS}=10V$ )	$T_C=25^\circ C$ 50	A
		$T_C=100^\circ C$ 35	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ C$ 51	W
		$T_C=100^\circ C$ 25	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.92	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	100	$^\circ C/W$
<b>Drain-Source Avalanche Ratings</b>			
$E_{AS}^{③}$	Avalanche Energy, Single Pulsed	81	mJ

**Electrical Characteristics** ( $T_C=25^{\circ}\text{C}$  Unless Otherwise Noted)

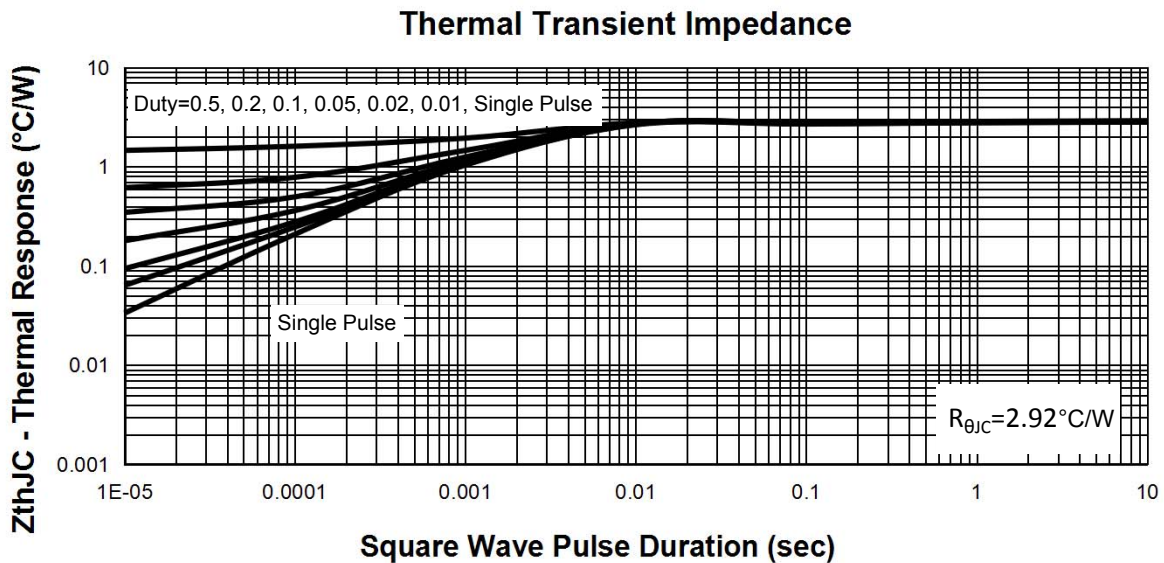
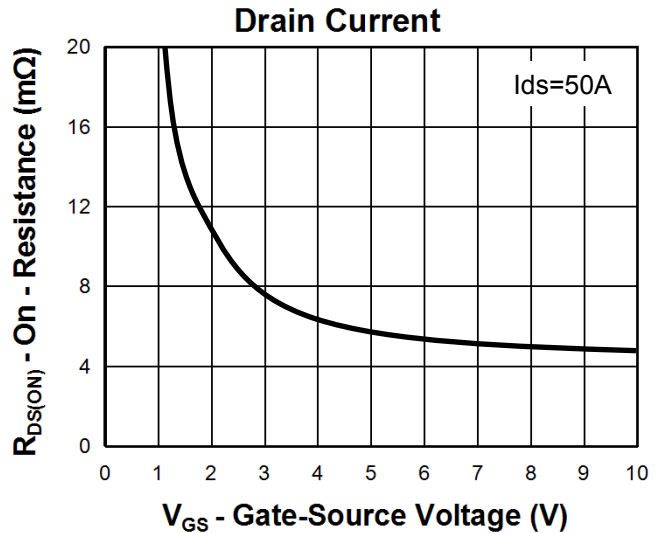
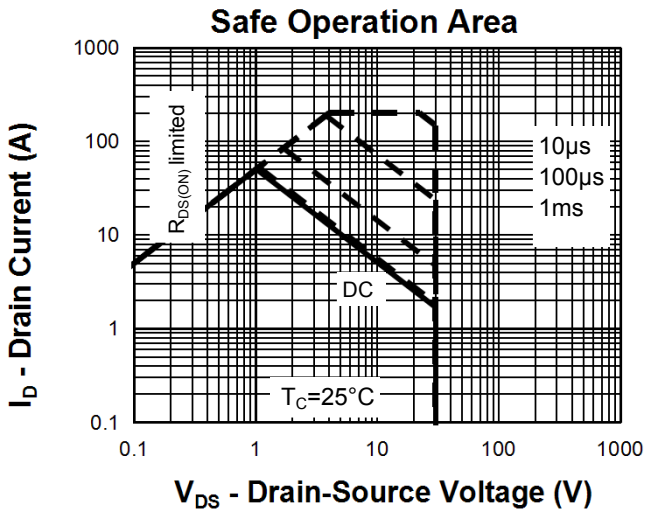
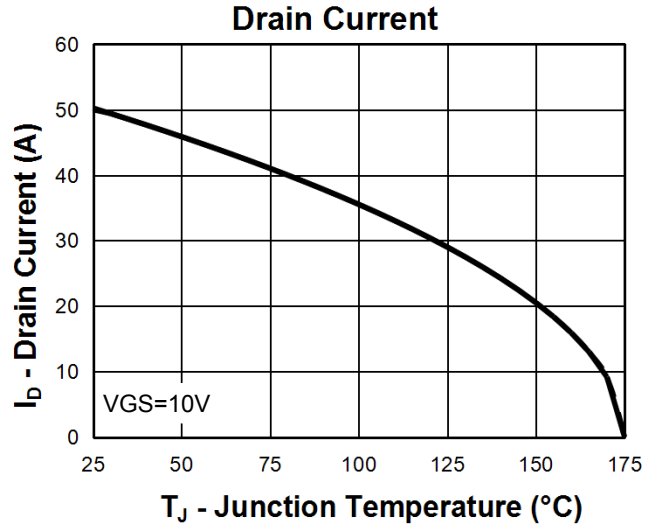
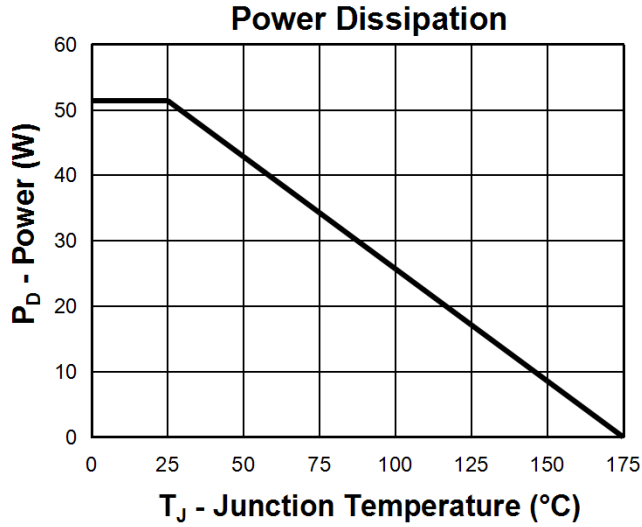
Symbol	Parameter	Test Condition	RUH3051L			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	$\mu A$
		$T_J=125^{\circ}\text{C}$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1		3	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$R_{DS(ON)}^{③}$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=35A$		6.8	8	$m\Omega$
		$V_{GS}=10V, I_{DS}=50A$		4.8	5.5	$m\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^{③}$	Diode Forward Voltage	$I_{SD}=50A, V_{GS}=0V$			1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=50A, di_{SD}/dt=100A/\mu s$		9		ns
$Q_{rr}$	Reverse Recovery Charge			15		nC
<b>Dynamic Characteristics</b> <sup>⑤</sup>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.3		$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=15V,$ Frequency=1.0MHz		580		pF
$C_{oss}$	Output Capacitance			130		
$C_{riss}$	Reverse Transfer Capacitance			65		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, I_{DS}=50A,$ $V_{GEN}=10V, R_G=4.7\Omega$		6		ns
$t_r$	Turn-on Rise Time			12		
$t_{d(OFF)}$	Turn-off Delay Time			16		
$t_f$	Turn-off Fall Time			5		
<b>Gate Charge Characteristics</b> <sup>⑤</sup>						
$Q_g$	Total Gate Charge	$V_{DS}=24V, V_{GS}=10V,$ $I_{DS}=50A$		14		nC
$Q_{gs}$	Gate-Source Charge			4		
$Q_{gd}$	Gate-Drain Charge			5		

- Notes:
- ①Pulse width limited by safe operating area.
  - ②Limited by  $T_{Jmax}$ ,  $I_{AS}=18A$ ,  $V_{DD}=24V$ ,  $R_G=50\Omega$ , Starting  $T_J=25^{\circ}\text{C}$ .
  - ③Pulse test ; Pulse width300s, duty cycle2%.
  - ④Guaranteed by design, not subject to production testing.

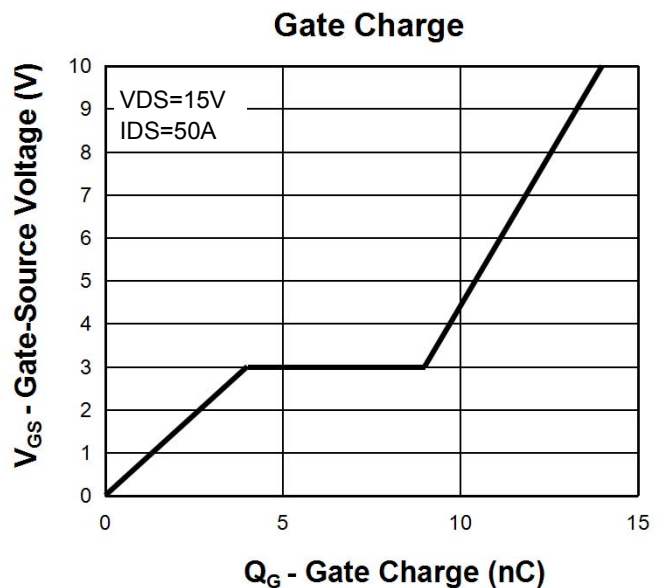
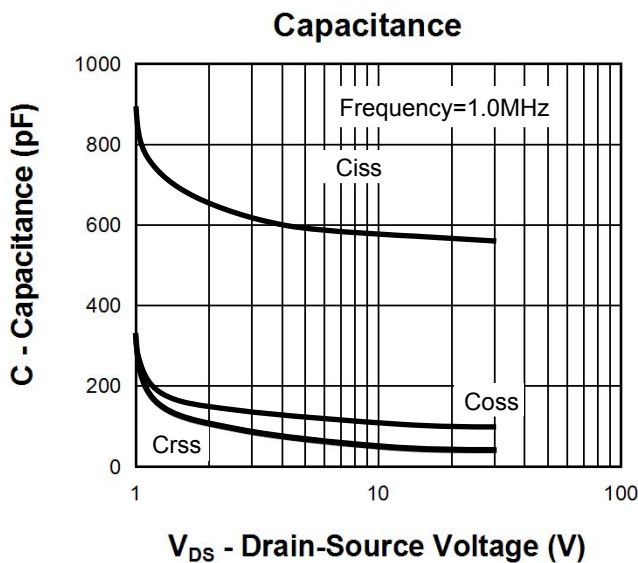
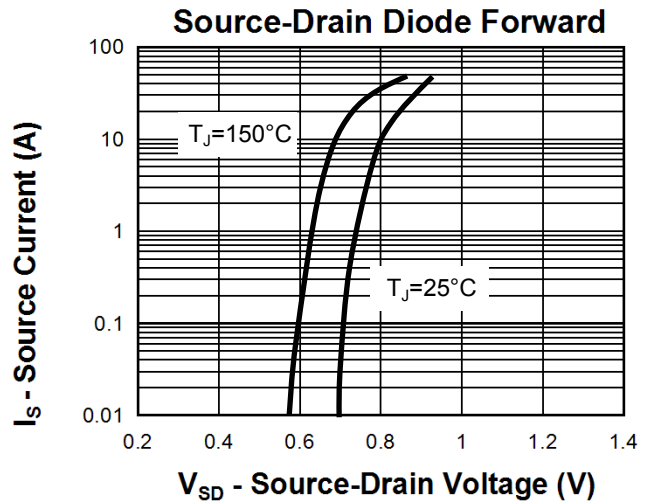
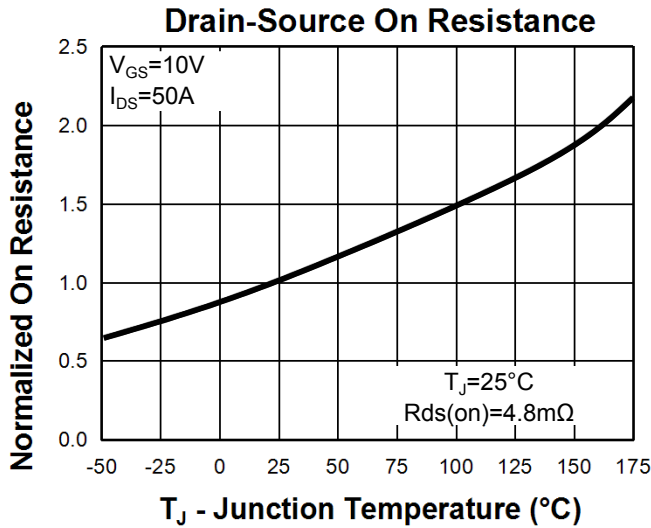
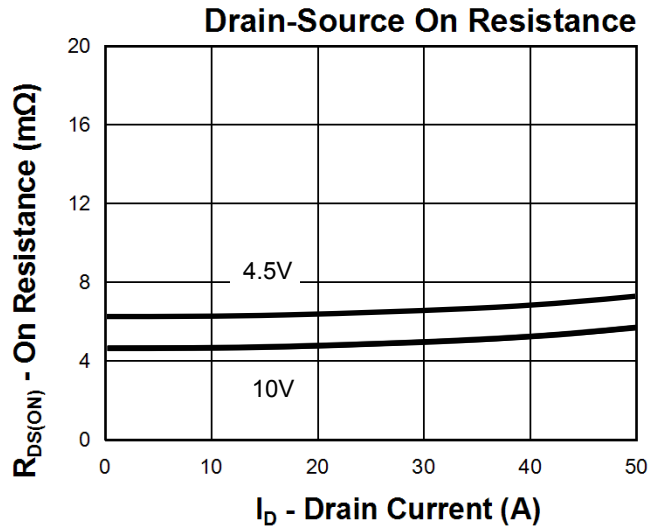
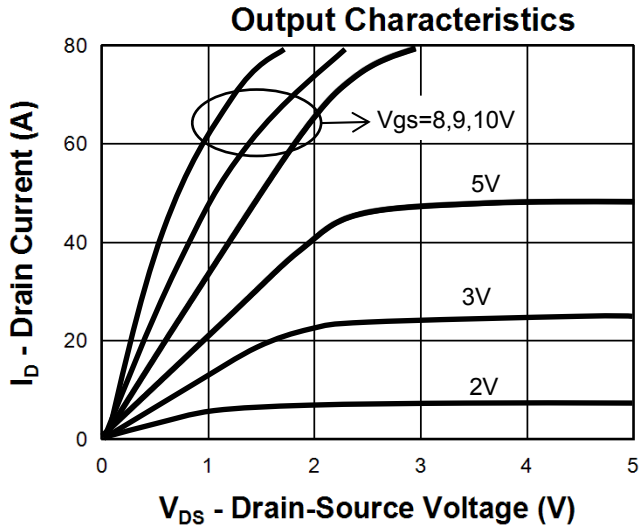
**Ordering and Marking Information**

<b>Device</b>	<b>Marking</b>	<b>Package</b>	<b>Packaging</b>	<b>Quantity</b>	<b>Reel Size</b>	<b>Tape width</b>
RUH3051L	RUH3051L	TO252	Tape&Reel	2500	13"	16mm

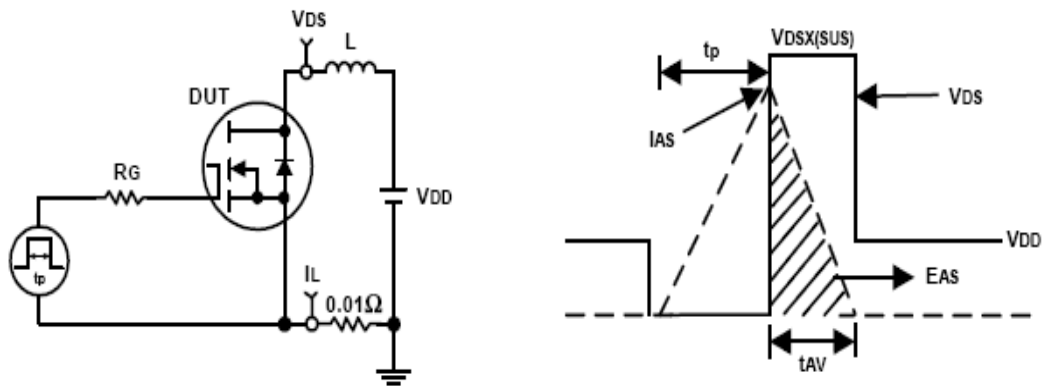
**Typical Characteristics**



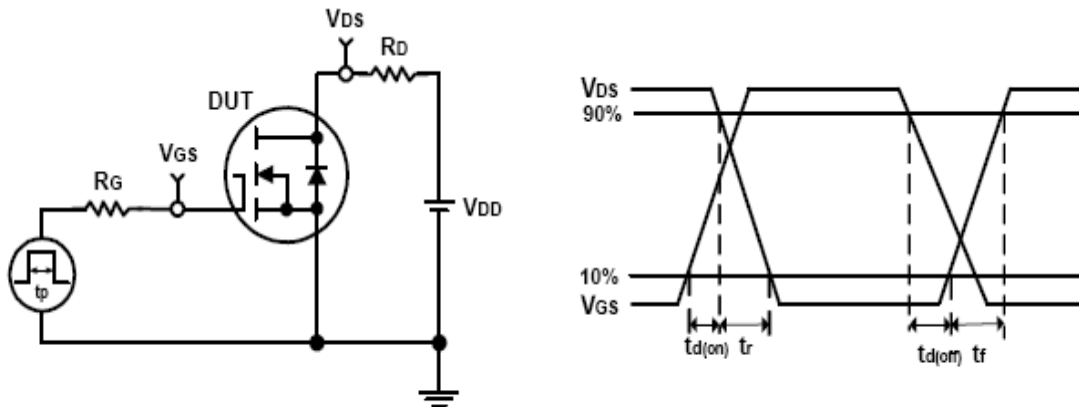
**Typical Characteristics**



**Avalanche Test Circuit and Waveforms**

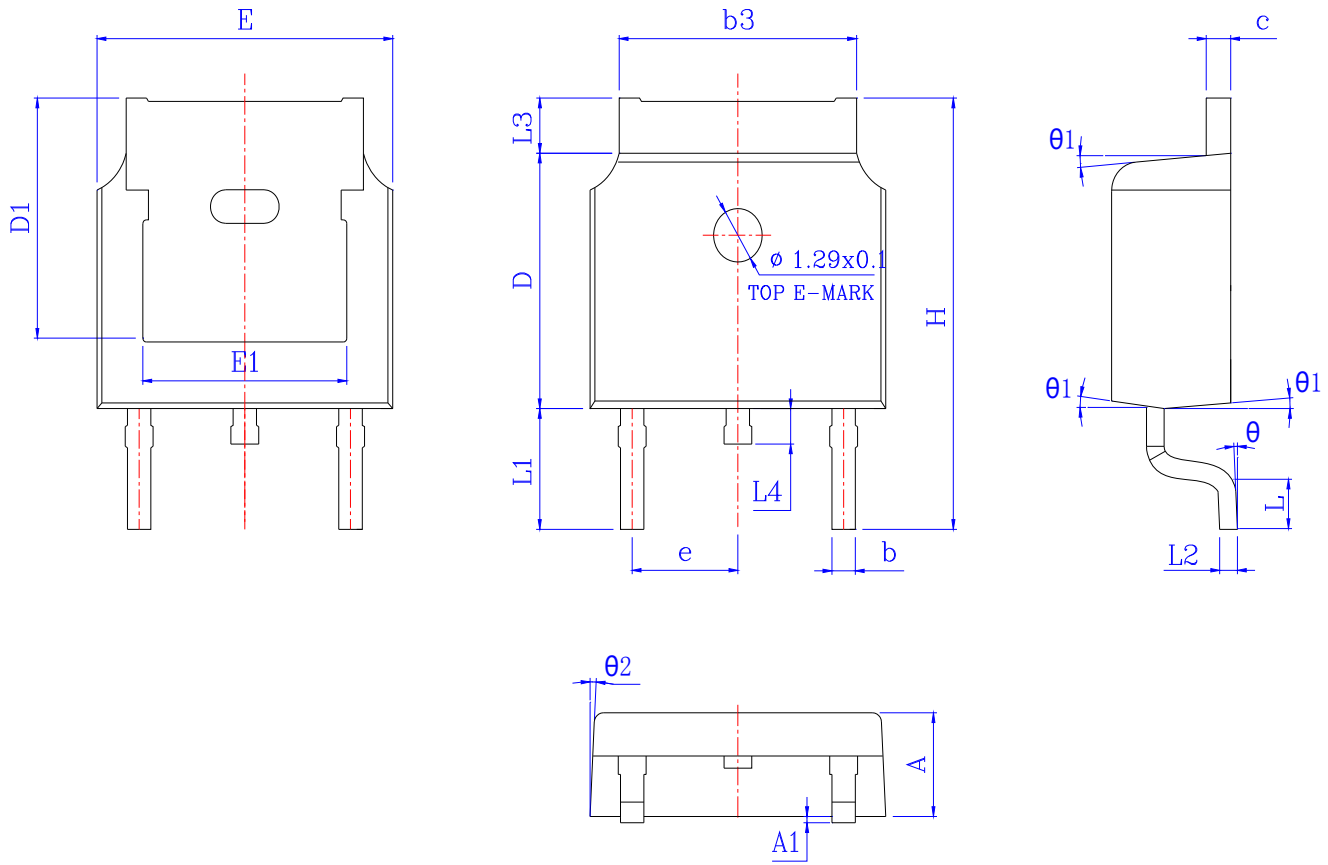


**Switching Time Test Circuit and Waveforms**



**Package Information**

**TO252**



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.200	2.300	2.400	0.087	0.091	0.094
A1	*	*	0.100	*	*	0.004
b	0.660	0.760	0.860	0.026	0.030	0.034
b3	5.130	5.295	5.460	0.202	0.208	0.215
c	0.470	0.535	0.600	0.019	0.021	0.024
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.30 REF			0.20 REF		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.700	4.810	4.920	0.185	0.189	0.194
e	2.28 REF			0.09 REF		
H	9.800	10.100	10.400	0.386	0.398	0.409
L	1.400	1.550	1.700	0.055	0.061	0.067
L1	2.743 REF			0.108 REF		
L2	0.510 BSC			0.020 BSC		
L3	0.900	1.075	1.250	0.035	0.042	0.049
L4	0.600	0.800	1.000	0.024	0.031	0.039
theta	0°	*	8°	0°	*	8°
theta 1	5°	7°	9°	5°	7°	9°
theta 2	5°	7°	9°	5°	7°	9°

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